



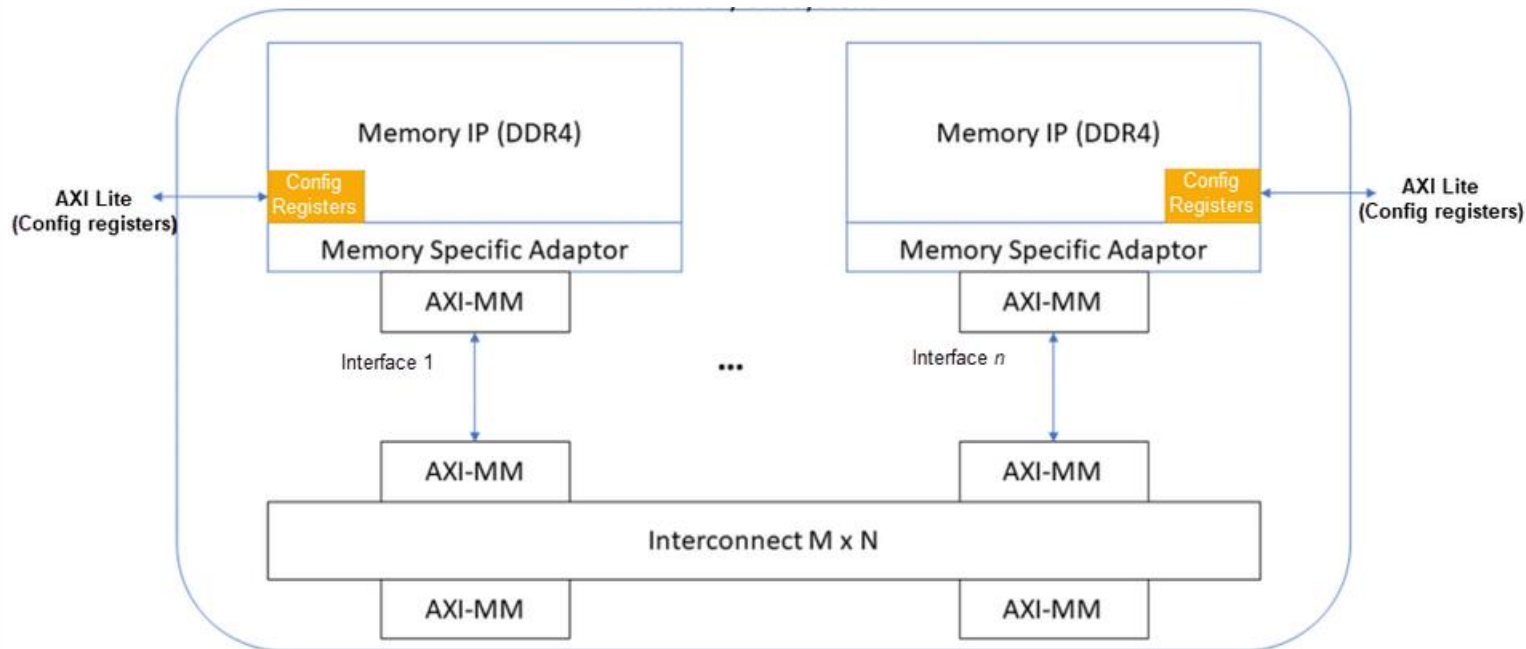
Embedded Systems
Hardware Design

Memory subsystems



Memory subsystem

The memory subsystem IP is a high-level solution on top of the External Memory Interfaces.

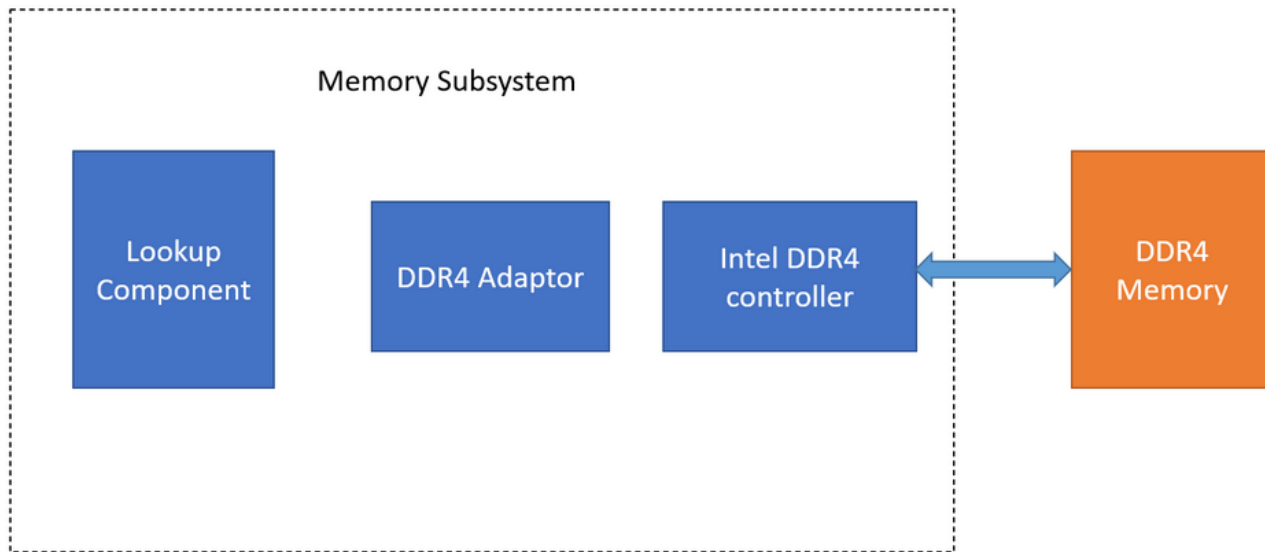


Source <https://www.intel.com/content/www/us/en/docs/programmable/789389/24-1-2-0-0/introduction-to-memory-subsystem-ip.html>



Memory Subsystem IP Used as Memory Adaptor with Lookup and One EMIF

The memory subsystem IP can be configured for use in various applications such as full crossbar for machine learning, multi-hierarchy memory bridge, or as a memory-specific adaptor with lookup core logic. All the available modes offer common scalability and compose-ability.



Source <https://www.intel.com/content/www/us/en/docs/programmable/789389/24-1-2-0-0/introduction-to-memory-subsystem-ip.html>



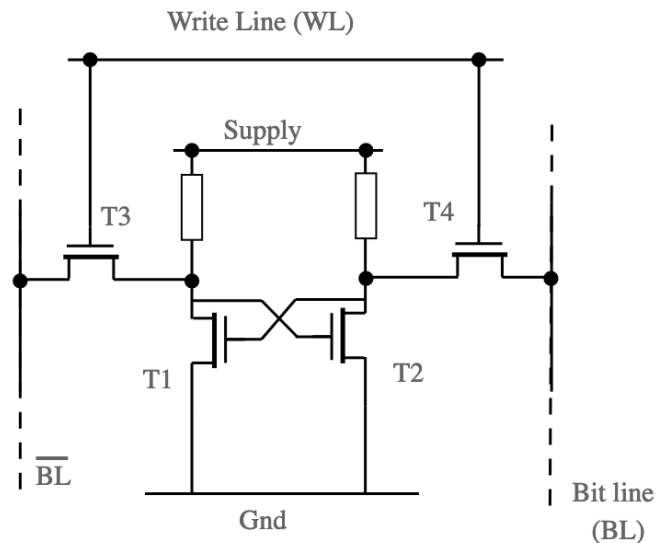
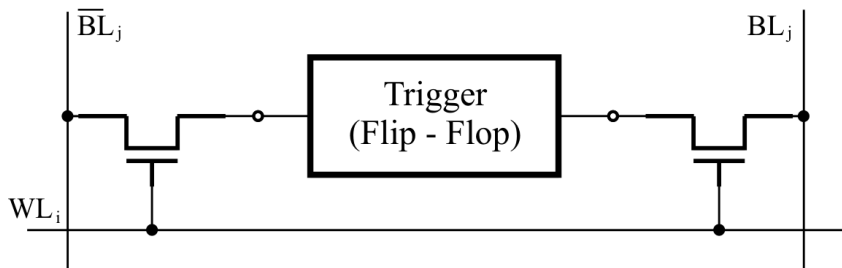
Types

- ROM
 - PROM
 - EPROM
 - EEPROM
- RAM
 - SRAM
 - DRAM
 - Synchronous
 - DDR – Double data rate
 - NVRAM (non-volatile RAM)



Static RAM

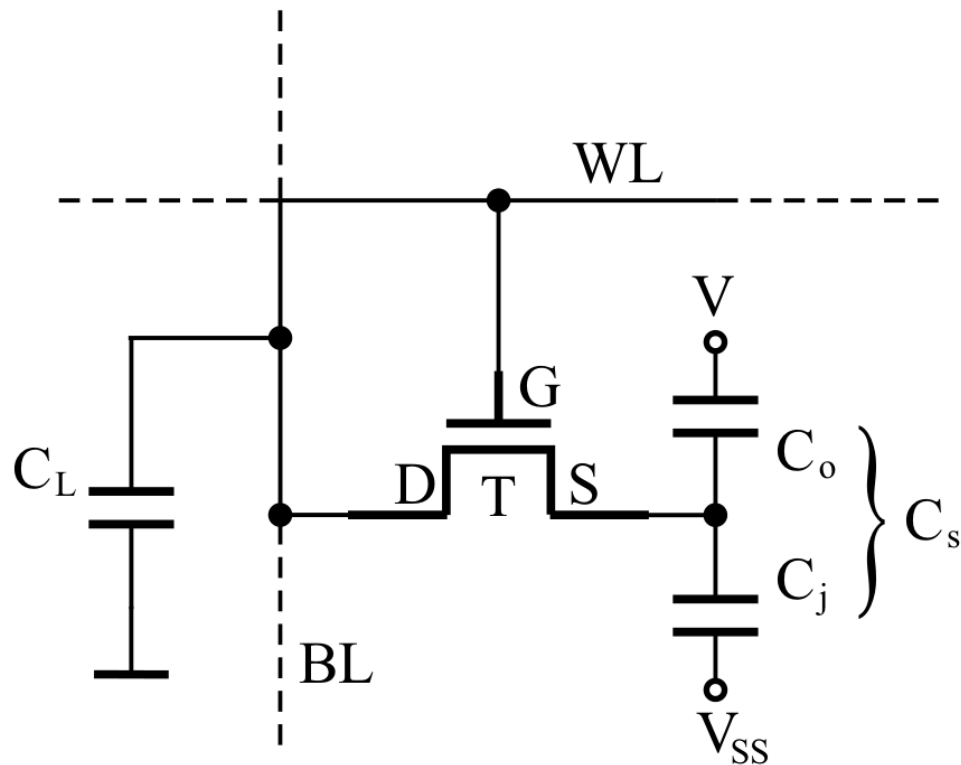
- Uses SR-Latches
- Expensive
- Doesn't need refreshing





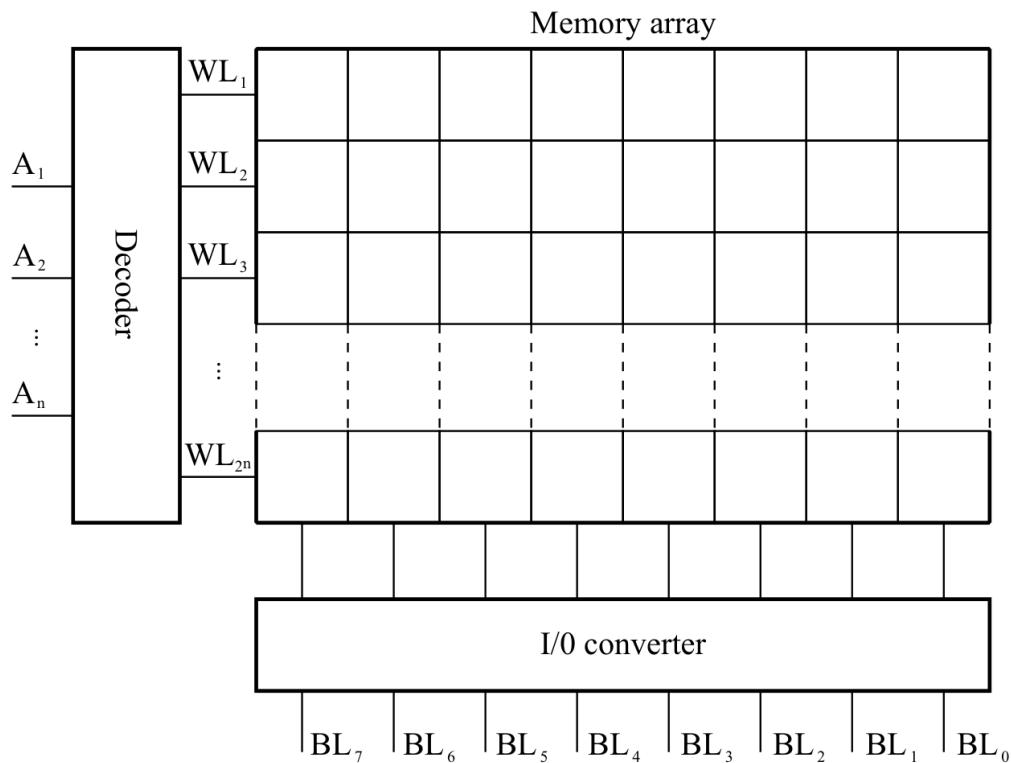
Dynamic RAM

- Uses small capacitors (with transistors)
- Requires constant refreshing
- Cheap





Digital memory architecture





Max supported memory & the '4GB limit'

- Address lines ~ Bits
- 16 bit $\Rightarrow 2^{16} = 65,536$ bytes (64 KiB)
- 32 bit $\Rightarrow 2^{32} = 4,294,967,296$ bytes (4 GiB)
- 64 bit $\Rightarrow 2^{64} = 18,446,744,073,709,551,616$ bytes (16 EiB)
- KiB \neq KB, GiB \neq GB, EiB \neq EB
 - KB, MB, GB, PB, EB – 1000 as a base
 - KiB, MiB, GiB, PiB, EiB – 1024 as a base
 - 1 MB = 0.953 MiB
 - 1.073 TB = 1 TiB



PAE

- Physical address extension
- Allows 32-bit OS to address more than 4GiB of memory
 - From 2^{32} to 2^{36} bytes
- Requires OS, CPU and motherboard chipset support.
- e.g. 32bit OS - Windows Server 2008 Enterprise, Datacenter can address up to 64 GB of memory



RAM

- RAM – Random Access Memory
- DRAM – Dynamic RAM
- SRAM – Static RAM
- SDRAM - Synchronous DRAM
- DDR – Double Data Rate (data is transferred on both rising and falling edges of the system's memory clock)



(S)DRAM

- SDR SDRAM (Single Data Rate)
- DDR SDRAM (Double Data Rate)
- DDR2 SDRAM
- DDR3 SDRAM
- DDR4 SDRAM
- DDR5 SDRAM



Formfactors

- DIMM - Dual In-Line Memory Module
- SODIMM – Small Outline DIMM
- CAMM/LPCAMM - Compression Attached Memory Module
- Soldered



Physical Differences DDR 1, 2, 3, 4 DIMMS

184 PINS

DDR 1

240 PINS

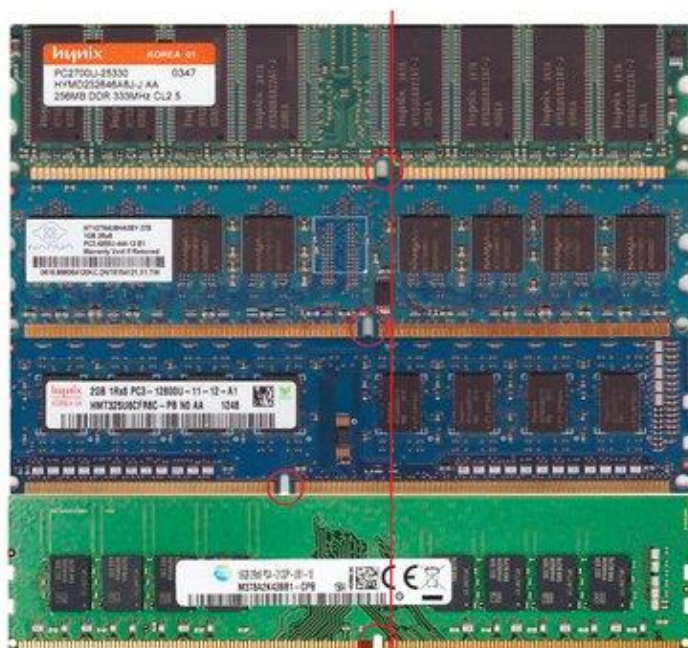
DDR 2

240 PINS

DDR 3

288 PINS

DDR 4



Note: DDR 4 RAM also has a slight bow in the row of pins.



SODIMM



DIMM



SO-DIMM

Every standard (SDRAM, DDR{1..5}) has its own SODIMM version – notch in different spots

DDR3 240/204pin Converter



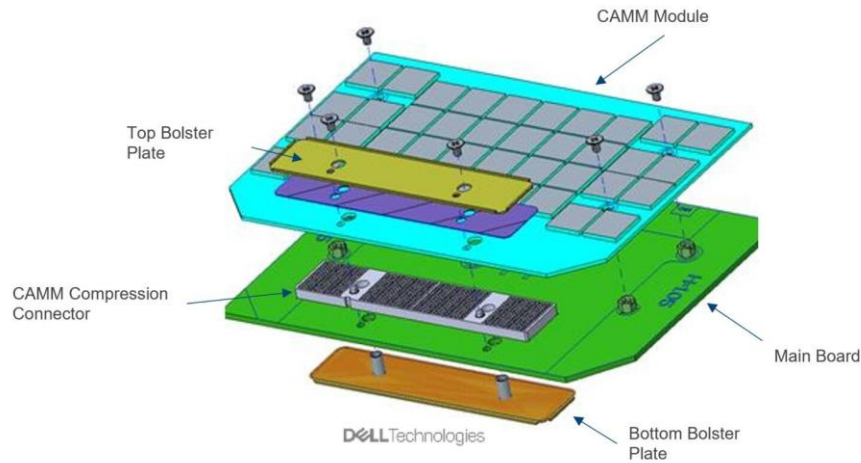
SODIMM can be used in DIMM slot using an adapter – same signals, different form-factor



CAMM



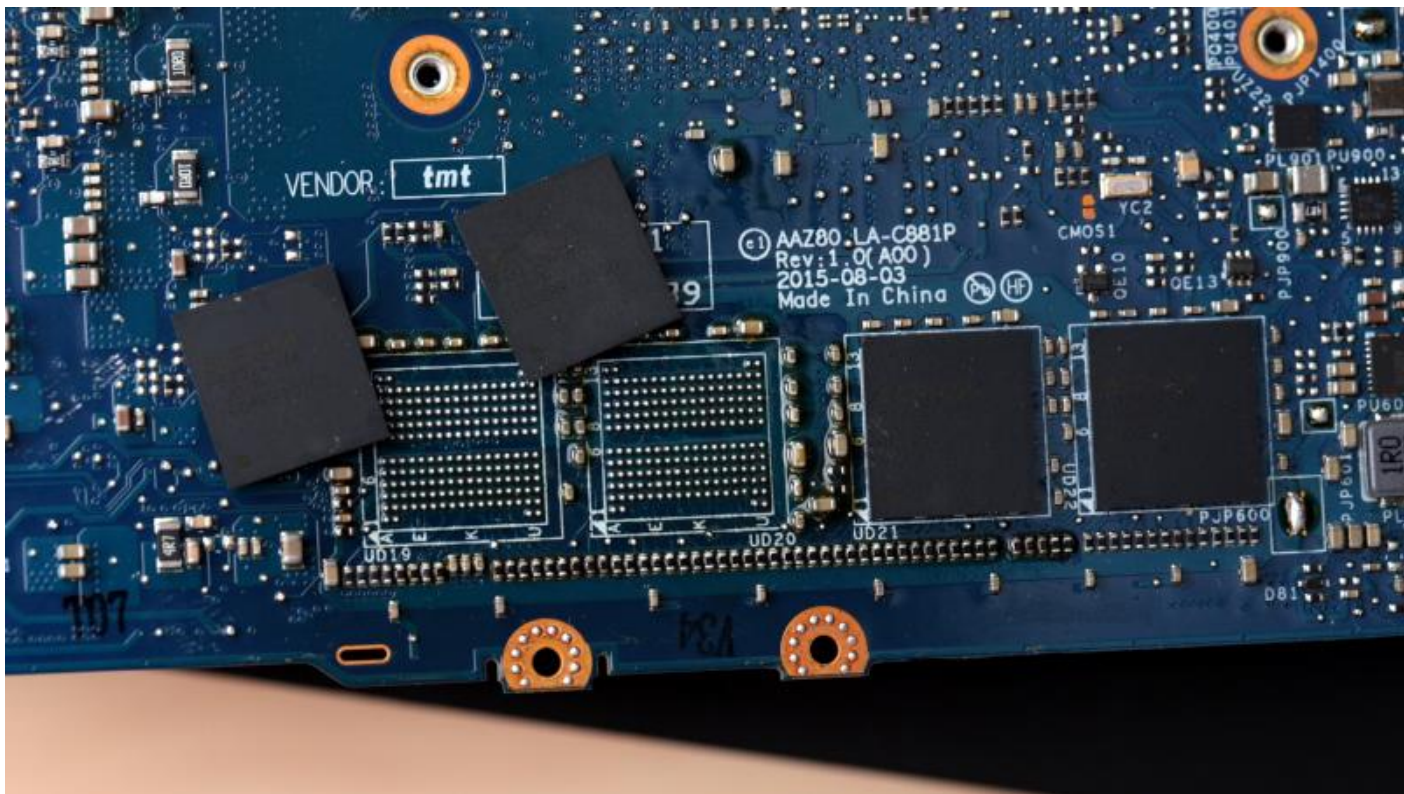
- Thinner than SODIMM (~57% thinner)
- Shorter traces (can be faster)
- Replacable/upgradable (vs soldered RAM)



Source: <https://www.extremetech.com/computing/334676-dell-offers-additional-insight-on-its-new-camm-memory-modules>



Soldered



Source: <https://hackaday.com/2021/11/24/you-cant-upgrade-soldered-on-laptop-ram-think-again/>



Voltage

- DDR (2.6V, 2.5V)
- DDR2 (1.8V)
- DDR3 (1.5V), DDR3L (1.35V)
- DDR4 (1.2V), ~~DDR4L (1.05V)~~
- DDR5 (1.1V)



DDR3L

- Lower required voltage – less power consumption
- Can work at both 1.35V and 1.5V (compatible with systems using DDR3 not 'L')
- Some systems doesn't work with DDR3 and require DDR3L



LPDDR

- Low power DDR
- Aimed at mobile devices
- DDR3L vs LPDDR3
- LPDDR4(x)
- LPDDR5(x)
- LPDDR6 ~2024/2025



Properties of the different LPDDR generations

LPDDR	1	1E	2	2E	3	3E	4	4X	5	5X
Maximum density (bit)					32		64	64	32	32
Memory array clock (MHz)	200	266	200	266	200	266	200	266	400	533
Prefetch size	$2n$		$4n$		$8n$		$16n$			
Memory densities			64 Mbit – 8 Gbit		1–32 Gbit		4–32 Gbit		4–32 Gbit	
I/O bus clock frequency (MHz)	200	266	400	533	800	1067	1600	2133	3200	4267
Data transfer rate, DDR (MT/s)^[a]	400	533	800	1067	1600	2133	3200	4267	6400	8533
Supply voltages (volts)	1.8		1.2, 1.8		1.2, 1.8		1.1, 1.8	0.6, 1.1, 1.8	0.5, 1.05, 1.8	0.5, 1.05, 1.8
Command/address bus	19 bits, SDR		10 bits, DDR				6 bits, SDR		7 bits, DDR	
Year	2006		2009		2012		2014	2017	2019	2021



LPDDR in Samsung phones

- S23 (2022) LPDDR5X
- S21 (2020) LPDDR5
- S10 (2019) LPDDR4X
- S7 (2016) LPDDR4
- S5 (2014) LPDDR3
- S2 (2011) LPDDR2





Types

- UDIMM – unbuffered/unregistered DIMM
 - Most consumer memory
 - Rarely with ECC
- RDIMM – Registered DIMM
 - Additional register chip (buffer) is added between DRAM chips and MC.
 - Allows for more DRAM chips on one DIMM (reduces electrical load on the control lines)
 - Usually has ECC capabilities
- LRDIMM – Load Reduced DIMM
 - Similar to RDIMM, but also data lines are buffered



ECC memory

- ECC - Error correction codes
- Used to detect and fix memory errors
- Protects against 'bit-flips'
 - 1-bit errors are detected and are transparently corrected
 - 2-bit errors are detected and cannot be corrected

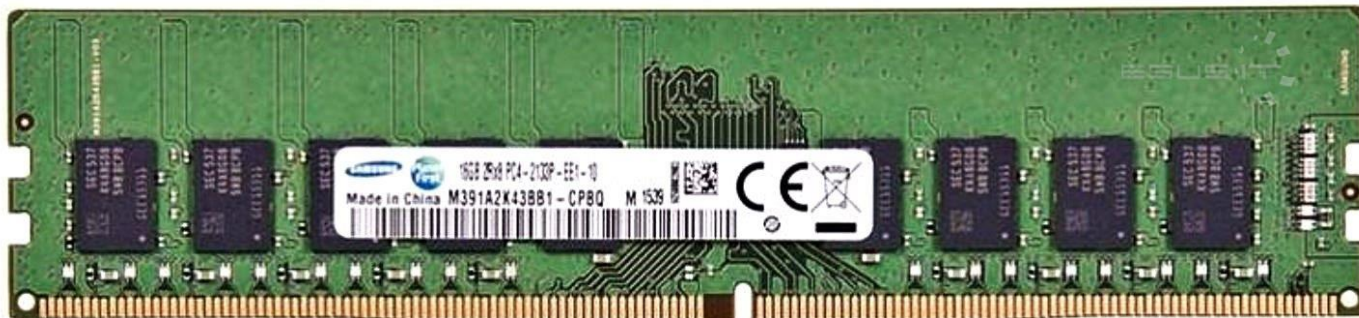


Systems' memory requirements

- Some platforms require the use of RDIMM
 - Since DDR5: RDIMM is keyed differently to UDIMM
- UDIMM platform cannot use RDIMM
- Non-ECC UDIMM platforms can still use ECC UDIMMs
- To use ECC of UDIMM - CPU and Chipset need to support ECC features.



UDIMM – ECC vs non-ECC





RDIMM



Additional register chip (buffer) in the middle of a module



Supported Memory Type for Intel Core Desktop Processors

- DDR3: 1st – 7th gen
- DDR4: 6th – 14th gen
- DDR5: 12th – 14th gen
- Most CPUs support two memory standards
 - Only one can be used at one time
 - Different motherboards can use different memory type for the same CPU
- <https://www.intel.com/content/www/us/en/support/articles/000094585/processors.html>



Motherboards with two memory types



SDRAM and DDR(1) slots on P4VMM2
Only one type can be used at once (or it doesn't POST)



GDDR SDRAM

- GDDR Graphics Double Data Rate SDRAM
 - DDR SGRAM
 - GDDR2
 - GDDR3
 - GDDR4
 - GDDR5
 - GDDR6
 - GDDR7



Detection


- SPD – Serial presence detection
- Simply flash memory (EEPROM)
- Uses SMBUS (~I²C, also for temp. sensors on DIMMs)
- Contains: model name, specifications, supported timings, (optionally) XMP timings (Extreme Memory Profile)
- JEDEC Standard 21-C section 4.1.2.4 "SPDs for DDR SDRAM"





HWINFO64 @ ASRock Z170 Extreme7+ - System Summary

CPU




Intel Core i7-6700K
Cores: 4
Stepping: R0
Logical: 8
Codename: Skylake-S
µCU: 74
SSPEC: SR2BR, SR2L0
Prod. Unit:
Platform: LGA1151
Cache: 4 x (32 + 32 + 256) + 8M
TDP: 95 W

Features

MMX	3DNow!	3DNow!-2	SSE	SSE-2	SSE-3	SSSE-3
SSE4A	SSE4.1	SSE4.2	AVX	AVX2	AVX-512	
BMI2	ABM	TBM	FMA	ADX	XOP	
DEP	VMX	SMX	SMEP	SMAP	TSX	MPX
EM64T	EIST	TM1	TM2	HTT	Turbo	SST
AES-NI	RDRAND	RDSEED	SHA	SGX		

Operating Point	Clock	Ratio	Bus	VID
CPU LFM (Min)	800.0 MHz	x8	100.0 MHz	-
CPU HFM (Max)	4000.0 MHz	x40	100.0 MHz	-
CPU Turbo	4200.0 MHz	x42	100.0 MHz	-
CPU Status	-	-	101.0 MHz	1.2749 V
Ring Max	4100.0 MHz	x41.00	100.0 MHz	-
Ring Status	4140.1 MHz	x41.00	101.0 MHz	-
System Agent Status	807.8 MHz	x8.00	101.0 MHz	-

GPU



MSI GTX 1060 ARMOR OC
NVIDIA GeForce GTX 1060 6GB
GP106-400
PCIe v3.0 x16 (8.0 GT/s) @ x8 (2.5 GT/s)
GPU #0: 6 GB
GDDR5 SDRAM
192-bit
ROPs / TMUs: 48 / 80
Shaders: Unified: 1280
Current Clocks (MHz): GPU 227.5, Memory 202.5, Video 544.0

Memory Modules

[#0] Corsair CMK32GX4M2A2666C16

Size	16 GB	Clock	1333 MHz	ECC	N		
Type	DDR4-2666 / PC4-21300 DDR4 SDRAM UDIMM						
Freq	CL	RCD	RP	RAS	RC	Ext.	V
1066	15	15	15	36	50	-	1.20
1000.0	14	14	14	33	47	-	1.20
933.3	13	13	13	31	44	-	1.20
866.7	12	12	12	29	41	-	1.20
800.0	11	11	11	27	38	-	1.20
733.3	10	10	10	25	35	-	1.20
666.7	9	9	9	22	31	-	1.20
600.0	9	9	9	20	28	-	1.20
1333	16	18	18	35	53	XMP	1.20
1200	15	17	17	32	48	YMP	1.20

Memory

Size: 64 GB, Type: DDR4 SDRAM
Clock: 1077.1 MHz = 10.67 x 101.0 MHz
Mode: Dual-Channel, CR 2T
Timing: 15 - 15 - 15 - 36 tRC tRFC 374

Operating System

Legacy Boot
Microsoft Windows 10 Professional (x64) Build 14393.576 (RS1)

Motherboard

ASRock Z170 Extreme7+

Chipset

Intel Z170 (Skylake PCH-H)

BIOS Date

09/05/2016

BIOS Version

P7.10

UEFI

UEFI

Drives

- ✓ SATA 6 Gb/s Samsung SSD 850 PRO 512GB [512 GB]
- ✓ SATA 6 Gb/s Samsung SSD 850 PRO 512GB [512 GB]
- ✓ NVMe INTEL SSDPEDMW400G4 [400 GB]
- ✓ NVMe Samsung SSD 950 PRO 512GB [512 GB]
- ✓ SATA 6 Gb/s WDC WD60EFRX-68MYMN1 [6001 GB]
- ✓ SATA 6 Gb/s Samsung SSD 850 PRO 256GB [256 GB]
- ✓ SATA 6 Gb/s SanDisk SDSSDXPS960G [960 GB]



Memory training

- MRC – Memory reference code
- Q: How to run code (MRC) when memory is not yet available?
- A: Use CAR – ‘Cache as RAM’



Memory controller

- In the past: dedicated chip (integrated in north bridge)
- Present: integrated into CPU-package
 - Called IMC (Integrated Memory Controller)
- Responsible for refreshing memory cells
- Takes the memory address as an input and fetches/writes data from/to main memory (DRAM).
- Usually integrated with MMU (memory management unit)



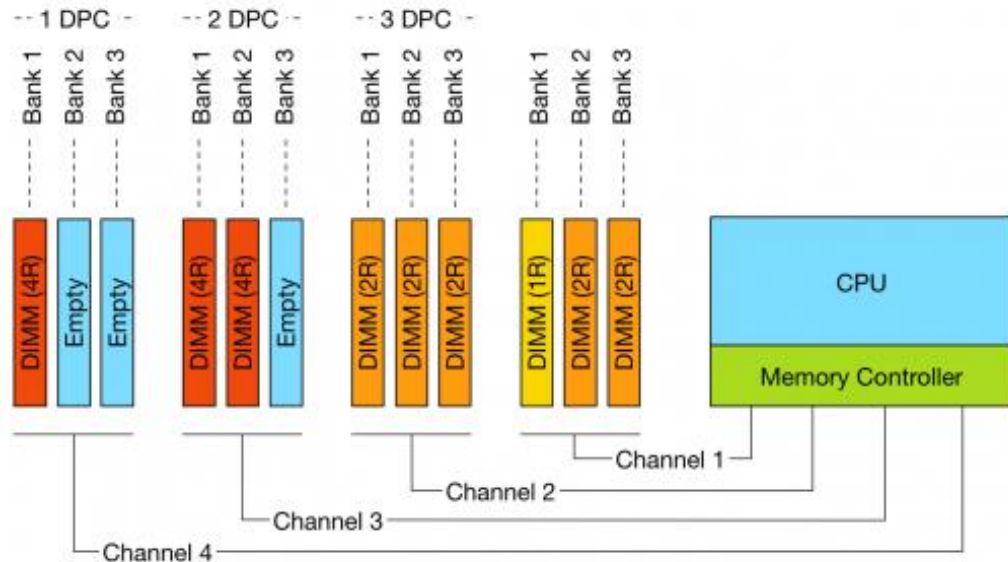
Multi-channel memory architecture

- MC has to support additional channels
- Requires specific memory configuration
 - At least two modules for Dual-Channel
 - Three for Triple-Channel, four for Quad-Channel
 - Some implementations allow for 'Flexible mode'
 - different modules' capacity
- Dual/Triple/Quad-Channel interleaved
 - spreads the data among different modules
 - allows for greater speeds
- DDR5 has additionally introduced sub-channels



Multi-Channel, multi-dimm

- DPC
 - DIMMs per channel
- MC can use only one DIMM in a channel at the same time





Attacks/mitigations

- Cold-boot attacks
- Rowhammer
 - Memory scrambling
 - Intel's Total Memory Encryption
 - Memory scrubbing
 - ECC



Memory timings

- CL – CAS Latency
 - CAS = Column Address Strobe
- T_{RCD} - Row Address to Column Address Delay
- T_{RP} - Row Precharge Time
- T_{RAS} - Row Active Time (Row Address Strobe)
- Usually presented in 'number of clock-cycles'



Memory timings

- Format: XX-XX-XX-XX
 - 1) CL
 - 2) tRCD
 - 3) tRP
 - 4) tRAS
 - Some can be omitted
- CL=11, tRCD=12
 - F3 is manufacturer specific info
- Note: 12800S => 1600Mhz





Combining Memory modules

- To make word larger
- To add more address lines



Additional materials

- <https://www.atpinc.com/blog/DDR5-dimm-types-rdimm-vs-udimm-for-server-platform>
- <https://frankdenneman.nl/2015/02/18/memory-tech-primer-memory-subsystem-organization/>
- <https://www.youtube.com/watch?v=7J7X7aZvMXQ>